Anomalous activation of shallow B+ implants in Ge

B.R. Yates a,⁎, B.L. Darby a, N.G. Rudawski a, K.S. Jones a, D.H. Petersen b, O. Hansen b,c, R. Lin d, P.F. Nielsen d, A. Kontos e

a Department of Materials Science and Engineering, University of Florida, Gainesville, FL 32611-6400, United States
b Department of Micro- and Nanotechnology, Technical University of Denmark, DTU Nanotech, Building 345B, DK-2800 Kgs. Lyngby, Denmark
c Center for Individual Nanoparticle Functionality, CNF, Technical University of Denmark, DK-2800 Kgs. Lyngby, Denmark
d CAPRES A/S, Scion-DTU, DK-2800 Kgs. Lyngby, Denmark
e Varian Semiconductor Equipment Associates, Gloucester, MA 01930, United States

⁎ Corresponding author. Tel.: +1 352 846 3353; fax: +1 352 392 7219.
E-mail address: bradyates@ufl.edu (B.R. Yates).

Article history:
Received 3 May 2011
Accepted 28 July 2011
Available online xxxxx

Keywords:
Ge
B
Dopant activation
Micro four point probe
TEM

A R T I C L E  I N F O

A B S T R A C T

The electrical activation of B+ implantation at 2 keV to doses of 5.0×10 13–5.0×10 15 cm -2 in crystalline and pre-amorphized Ge following annealing at 400°C for 1.0 h was studied using micro Hall effect measurements. Preamorphization improved activation for all samples with the samples implanted to a dose of 5.0×10 15 cm -2 displaying an estimated maximum active B concentration of 4.0×10 20 cm -3 as compared to 2.0×10 20 cm -3 for the crystalline sample. However, incomplete activation was observed for all samples across the investigated dose range. For the sample implanted to a dose of 5.0×10 13 cm -2, activation values were 7% and 30%, for c-Ge and PA-Ge, respectively. The results suggest the presence of an anomalous clustering phenomenon of shallow B+ implants in Ge.

© 2011 Elsevier B.V. All rights reserved.

1. Introduction

As the scaling associated with traditional Si metal oxide semiconductor (MOS) devices reaches fundamental limits, changes in MOS design or material composition are becoming necessary. Ge is a promising alternative material for next-generation MOS devices as its increased carrier mobility makes it an attractive replacement for Si [1]. In addition, its reduced melting temperature may allow for less aggressive annealing temperature which could prove advantageous for process integration of high-κ/metal gate device structures.

In the case of B, it is known that the equilibrium chemical solid solubility limit in Ge [2] is 5.5×10 18 cm -3 at 850°C, which is significantly lower compared to Si at the homologous temperature [3,4]. However, electrical activation in excess of this value was reported for B+-implantation into single-crystal (c) as well as pre-amorphized (PA) material [5–11]. For B+ implants at 35 keV into PA-Ge, complete activation was observed for all doses up to 7.6×10 15 cm -2 implying active B concentrations as high as 5.7×10 20 cm -3 following an anneal at 360°C for 1.0 h [10]. In the case of PA-Ge, annealing to induce solid-phase epitaxial growth (SPEG) of the amorphized layer results in the incorporation of a concentration of substitutional B greater than the equilibrium chemical concentration; analogous behavior was similarly reported for the case of B+-implantation into Si [12].

Although B activation has been characterized for deep B +- implantation into both c-Ge and PA-Ge, the activation of low energy B+–implantation in Ge remains poorly understood and characterized. In the few studies which utilized low energy B+–implantation, the activation level, if determined, was calculated indirectly by fitting resistance values to a mobility model [7,9,13]. This model was developed using Hall effect measurements and may suffer from possible error introduced from Hall scattering factor assumptions [14]. In order to accurately characterize the activation behavior, the sheet carrier density and mobility should be measured directly using a Hall effect technique.

Furthermore, characterization of shallow implant activation is very challenging with conventional four-point probe and Hall effect techniques partially due to high junction leakage [15–17]. Due to the smaller band gap of Ge compared to Si and the larger number of intrinsic carriers [1], junction leakage is increased for Ge [18,19] which exacerbates the characterization challenges. Recently, instruments and techniques have been developed which perform four-point probe and Hall effect measurements using probes with μm-scale spacing as described in detail elsewhere [17,20–22]; these micro four-point probe (M4PP) and micro Hall effect (MHE) measurements have been shown to greatly reduce the effects of junction leakage [15–17] and have previously been used for successful characterization of active shallow dopants in Ge [8,23]. In this work, the activation of low energy B+–implantation into c-Ge and PA-Ge was studied using M4PP and MHE measurements.

2. Experimental

Czochralski-grown n-type (001) wafers (resistivity: 50 Ω cm) were used for this work. A set of c-Ge samples was produced by...
B⁺-implantation at 2 keV to doses of $5.0 \times 10^{13}$–$5.0 \times 10^{15}$ cm$^{-2}$ while a set of PA-Ge samples was produced by first performing Ge⁺-implantation at 120 keV to a dose of $2 \times 10^{14}$ cm$^{-2}$ before the same B⁺-implantation step. In the case of PA-Ge samples, a continuous amorphous layer extending $100 \pm 2.5$ nm from the surface was produced as verified by high-resolution cross-sectional transmission electron microscopy (HR-XTEM). Samples were annealed in N$_2$ ambient at 400 °C for 1.0 h to activate the implanted B⁺. HR-XTEM was used to image the microstructure of the specimens before and after annealing with samples prepared using focused ion beam (FIB) milling. Secondary ion mass spectrometry (SIMS) was performed on selected samples to determine B concentration profiles before and after annealing.

3. Results and discussion

Sheet resistance, Hall sheet number ($n_s$), and Hall mobility ($\mu_H$) were measured using a CAPRES microRSP M-150 M4PP with Au-coated probes, a probe spacing of 20 μm, and a permanent magnet with a magnetic flux density of 0.475 T. Hall sheet number and mobility values were adjusted to obtain the carrier sheet number ($n_s$) and drift mobility ($\mu_d$) by using a scattering factor ($r_H$) of 1.21 as determined empirically by Mirabella et al. for high dose B⁺-implantation into Ge [10]. The carrier density and drift mobility are related to the Hall values by $n_s = n_H \times r_H$ and $\mu_d = \mu_H / r_H$, respectively.

Fig. 1 presents measured $R_s$ and $n_s$ values as a function of implanted B⁺ dose for both c-Ge and PA-Ge samples following annealing at 400 °C for 1.0 h. As shown in Fig. 1a, the $R_s$ value decreases with increasing B⁺ dose for both c-Ge and PA-Ge samples with c-Ge samples exhibiting higher sheet resistance values compared to the PA-Ge samples. The reduced $R_s$ values for the PA-Ge samples are explained by the increased solubility and B incorporation during SPEG as previously reported by others for different implant conditions [5–7]. The carrier sheet number is plotted as a function of implanted B⁺ dose for both c-Ge and PA-Ge samples after adjustment with a Hall scattering factor of 1.21 as shown in Fig. 1b; the PA-Ge samples exhibited higher $n_s$ values compared to c-Ge samples, similar to previous reports [5–7]. More interestingly, for B⁺ doses less than $5.0 \times 10^{15}$ cm$^{-2}$, the percent activation for both c-Ge and PA-Ge samples is relatively independent of dose at ~7 and ~30%, respectively. At a dose of $5.0 \times 10^{15}$ cm$^{-2}$, the difference in percent activation is much smaller, ~10 and 15% for c-Ge and PA-Ge samples, respectively. Fig. 2 shows HR-XTEM images of a c-Ge sample B⁺-implanted at 2 keV to a dose of $5.0 \times 10^{15}$ cm$^{-2}$. As shown in Fig. 2a, a damage layer extending 18 ± 0.5 nm from the surface is evident, which matches well with the expected range [24] of the implant. At higher magnifications, as shown in Fig. 2b, amorphous pockets are evident within the damaged layer. Thus, the smaller difference in $R_s$ between c-Ge and PA-Ge for the case of a B⁺ dose of $5.0 \times 10^{15}$ cm$^{-2}$ is likely due to enhanced incorporation of substitutional B within the amorphous regions during SPEG upon annealing.

To better understand the activation behavior, samples B⁺-implanted to doses of $5.0 \times 10^{13}$ and $5.0 \times 10^{15}$ cm$^{-2}$ into c-Ge and PA-Ge were analyzed using SIMS before and after annealing to
determine B concentration profiles, as shown in Fig. 3. The measured B concentration profiles (both before and after annealing) were very similar to as-implanted simulations [24]. The maximum active concentration was estimated using the SIMS profile and the corresponding measured $n_i$ values presented in Fig. 1b as described elsewhere [6]. For c-Ge and PA-Ge samples B$^+$-implanted to a dose of $5.0 \times 10^{15}$ cm$^{-2}$, the maximum active B concentrations were estimated at 2.0×10$^{20}$ and 4.0×10$^{20}$ cm$^{-3}$, respectively; the value for PA-Ge is similar to prior results [5–10].

The observed activation behavior for both c-Ge and PA-Ge samples is very interesting; incomplete activation is observed for even the lowest B$^+$ doses in both sample sets. Based on the reported maximum active B concentration [10], full activation should be expected for B$^+$-implantation at 2 keV to a dose of $5 \times 10^{13}$ cm$^{-2}$ for both c-Ge and PA-Ge, yet the measured percent activation in each case was ~7 and ~30%, respectively. This is unexpected and may have resulted from chemical dose loss or a unique dopant clustering/precipitation that scales with B$^+$ dose.

One contributing factor for the low levels of activation is dose loss during implantation resulting from backscattering of the light B$^+$ ions from the much heavier Ge atoms. In fact, for B$^+$-implantation at 2 keV into Ge, simulations [24] predict a backscattering loss of ~20% of the implanted dose. Additionally, due to the shallow nature of the implant, even slight surface oxidation is capable of consuming a non-negligible portion of the implanted B$^+$ dose. HR-XTEM analysis revealed the presence of a 3.0 ± 0.2 nm-thick surface GeO$_2$ layer on all as-implanted samples, as shown in Fig. 2. As per simulations [24], ~8% of the implanted dose is rendered inactive via the presence of a GeO$_2$ layer of this thickness. Finally, it should be noted that the percent of dose rendered inactive due to both oxidation and ion backscattering should be independent of implanted dose; however, the combination of losses due to backscattering and surface oxidation can only account for ~28% of dose loss. Thus, the bulk of the inactive fraction cannot be explained by these factors.

A probable source of inactive B is due to clustering, which has been observed and extensively studied in Si [25,26]. In the case of Si, for a given processing condition, full activation is expected for low B$^+$ doses until a certain concentration threshold is reached after which clustering occurs. However, for the presented data, incomplete activation is observed with the percent activation remaining relatively constant for investigated doses below $5.0 \times 10^{15}$ cm$^{-2}$. Work by Impellizzeri et al. [11] and Bisognin et al. [27] revealed incomplete activation for B$^+$-implantation at 35 keV into c-Ge, which was attributed to the formation of a B-Ge cluster through the use of ion beam analysis and high-resolution X-ray diffraction, respectively. However, incomplete activation observed in this present work is much more pronounced and is observed in both c-Ge and PA-Ge samples. The physical explanation behind the observed anomalous activation behavior is unclear; however, the close proximity of the surface is a possible contributing factor. In comparing the results observed in this work with those by Impellizzeri et al. [10], the decrease in B$^+$ implant energy, or shifting the B profile closer to the surface, enhances the incomplete activation observed. Since it is known that defect production and annihilation can be influenced by surface proximity in Si [28], it is believed that the shallow nature of the implants in this work is exacerbating the incomplete activation observed through an enhanced formation of B-Ge clusters. For several decades, it has been known that the surface of Ge decomposes into a porous structure under high-dose irradiation [29]. Recently, it has been shown that self-implantation into Ge at a relatively modest dose of 2.0×10$^{15}$ cm$^{-2}$ and energy of 30 keV is sufficient to induce the formation of void clusters and the onset of the porous structure [30]. These results suggest that there may be a barrier to point defect recombination near the surface which may be promoting the formation of B-Ge clusters following shallow B$^+$ implantation in Ge. Further experiments are underway to identify the underlying mechanism behind the observed anomalous activation behavior.

4. Conclusions

In summary, the activation of B$^+$-implantation at 2 keV into crystalline and pre-amorphized Ge was studied using micro four-point probe and micro Hall effect measurements. For B$^+$ doses of $5.0 \times 10^{13}$–$5.0 \times 10^{15}$ cm$^{-2}$, pre-amorphized samples exhibited greater activation compared to crystalline samples following a 400 °C anneal for 1 h. In the case of B$^+$-implantation to a dose of $5.0 \times 10^{15}$ cm$^{-2}$, the discrepancy in activation between crystalline and pre-amorphized samples is much smaller; this was attributed to solid-phase epitaxial growth within amorphous pockets formed in crystalline samples as a result of only B$^+$-implantation. Interestingly, for both crystalline and pre-amorphized samples, the measured percent activation was approximately independent of implanted dose; this behavior is in stark contrast to reported activation behavior of shallow B$^+$-implantation in Si and deeper B$^+$-implantation in Ge. This indicates the possibility of a B activation mechanism which is unique to shallow B$^+$-implantation in Ge; the physical explanation of this anomalous behavior is unclear, though the close proximity of the surface to the implanted B$^+$ profile may be a contributing factor.

Acknowledgments

The authors acknowledge the Intel Corporation for funding this work and the Major Analytical Instrumentation Center at the University of Florida for use of the FIB and TEM facilities. CINF is sponsored by The Danish National Research Foundation.

References
